DDC (xxxx) U

NPN PRE-BIASED SMALL SIGNAL SOT-363 DUAL SURFACE MOUNT TRANSISTOR

NEW PRODUCT

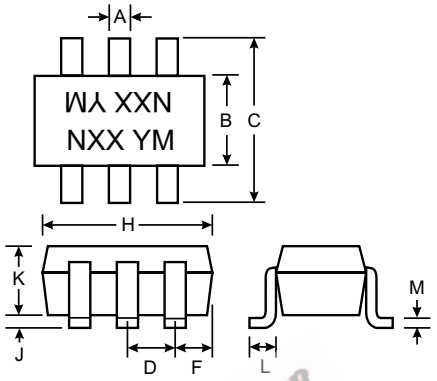
Features

UNDER DEVELOPMENT

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDA)
- Built-In Biasing Resistors

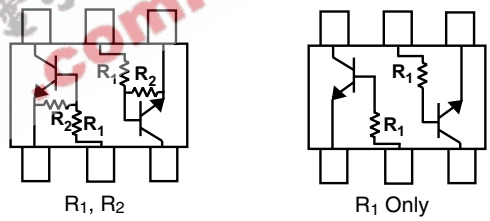
Mechanical Data

- Case: SOT-363, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.80	2.20
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

P/N	R1	R2	MARKING
DDC124EU	22K	22K	N17
DDC144EU	47K	47K	N20
DDC114YU	10K	47K	N14
DDC123JU	2.2K	47K	N06
DDC114EU	10K	10K	N13
DDC143TU	4.7K	-	N07
DDC114TU	10K	-	N12



SCHEMATIC DIAGRAM

Maximum Ratings

@ T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Supply Voltage, (3) to (1)		V_{CC}	50	V
Input Voltage, (2) to (1)	DDC124EU DDC144EU DDC114YU DDC123JU DDC114EU DDC143TU DDC114TU	V_{IN}	-10 to +40 -10 to +40 -6 to +40 -5 to +12 -10 to +40 -5 Vmax -5 Vmax	V
Output Current	DDC124EU DDC144EU DDC114YU DDC123JU DDC114EU DDC143TU DDC114TU	I_O	30 30 70 100 50 100 100	mA
Output Current	All	I_C (Max)	100	mA
Power Dissipation		P_d	200	mW
Operating and Storage and Temperature Range		T_j, T_{STG}	-55 to +150	°C

NEW PRODUCT

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic (DDC143TU & DDC114TU only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	I_C = 50μA
Collector-Emitter Breakdown Voltage	BV_{CEO}	50	—	—	V	I_C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	I_E = 50μA
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	V_{CB} = 50V
Emitter Cutoff Current	I_{EBO}	—	—	0.5	μA	V_{EB} = 4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.3	V	I_C/I_B = 2.5mA / 0.25mA DDC143TU I_C/I_B = 1mA / 0.1mA DDC114TU
DC Current Transfer Ratio	h_{FE}	100	250	600	—	I_C = 1mA, V_{CE} = 5V
Gain-Bandwidth Product*	f_T	—	250	—	MHz	V_{CE} = 10V, I_E = -5mA, f = 100MHz

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DDC124EU DDC144EU DDC114YU DDC123JU DDC114EU	$V_{I(off)}$	0.5 0.5 0.3 0.5 0.5	1.1 1.1 — — 1.1	—	V	V_{CC} = 5V, I_O = 100μA
	DDC124EU DDC144EU DDC114YU DDC123JU DDC114EU	$V_{I(on)}$	—	1.9 1.9 — — 1.9	3.0 3.0 1.4 1.1 3.0		V_O = 0.3, I_O = 5mA V_O = 0.3, I_O = 2mA V_O = 0.3, I_O = 1mA V_O = 0.3, I_O = 5mA V_O = 0.3, I_O = 10mA
Output Voltage	DDC124EU DDC144EU DDC114YU DDC123JU DDC114EU	$V_{O(on)}$	—	0.1	0.3	V	I_O/I_I = 10mA / 0.5mA I_O/I_I = 10mA / 0.5mA I_O/I_I = 5mA / 0.25mA I_O/I_I = 5mA / 0.25mA I_O/I_I = 10mA / 0.5mA
Input Current	DDC124EU DDC144EU DDC114YU DDC123JU DDC114EU	I_I	—	—	0.36 0.18 0.88 3.6 0.88	mA	V_I = 5V
Output Current		$I_{O(off)}$	—	—	0.5	μA	V_{CC} = 50V, V_I = 0V
DC Current Gain	DDC124EU DDC144EU DDC114YU DDC123JU DDC114EU	G_I	56 68 68 80 30	—	—	—	V_O = 5V, I_O = 5mA V_O = 5V, I_O = 5mA V_O = 5V, I_O = 10mA V_O = 5V, I_O = 10mA V_O = 5V, I_O = 5mA
Gain-Bandwidth Product*		f_T	—	250	—	MHz	V_{CE} = 10V, I_E = 5mA, f = 100MHz

* Transistor - For Reference Only